MAC3030-8

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave AC control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full−wave silicon gate controlled solid−state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 250 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes (Quadrants)
- Pb−Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off−State Voltage (Note 1) (T_J = −40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open)	V_{DRM}, V_{RRM}	250	V
On−State RMS Current (T_C = +70°C) Full Cycle Sine Wave 50 to 60 Hz	$I_{T(RMS)}$	8.0	A
Peak Non−Repetitive Surge Current (One Full Cycle, Sine Wave 60 Hz, T_C = +25°C) Preceded and followed by rated current	I_{TSM}	80	A
Circuit Fusing Considerations, (t = 8.3 ms)	I^2t	26	A^2s
Peak Gate Power (T_C = +70°C, Pulse Width = 10 μs)	P_{GM}	20	W
Average Gate Power (T_C = +70°C, t = 8.3 ms)	$P_{G(AV)}$	0.35	W
Peak Gate Current (T_C = +70°C, Pulse Width = 10 μs)	I_{GM}	2.0	A
Operating Junction Temperature Range	T_J	−40 to +125	°C
Storage Temperature Range	T_{stg}	−40 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

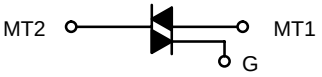
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

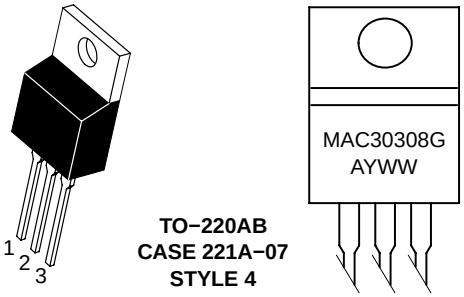
ON Semiconductor®

http://onsemi.com

TRIACS
8.0 AMPERES RMS
250 VOLTS



MARKING DIAGRAM



TO−220AB
CASE 221A−07
STYLE 4

MAC3030−8 = Standard Device Code
MAC30308G = Pb−Free Device Code
A = Assembly Location
Y = Year
WW = Work Week

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
MAC3030−8	TO−220AB	500 Units/Box
MAC3030−8G	TO−220AB (Pb−Free)	500 Units/Box

THERMAL CHARACTERISTICS

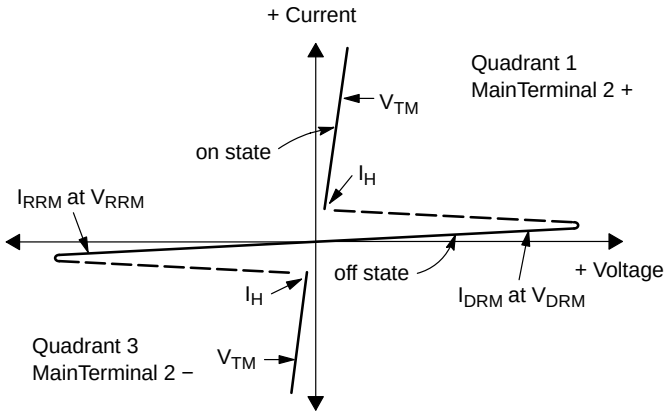
Characteristic	Symbol	Value	Unit
Thermal Resistance − Junction−to−Case − Junction−to−Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

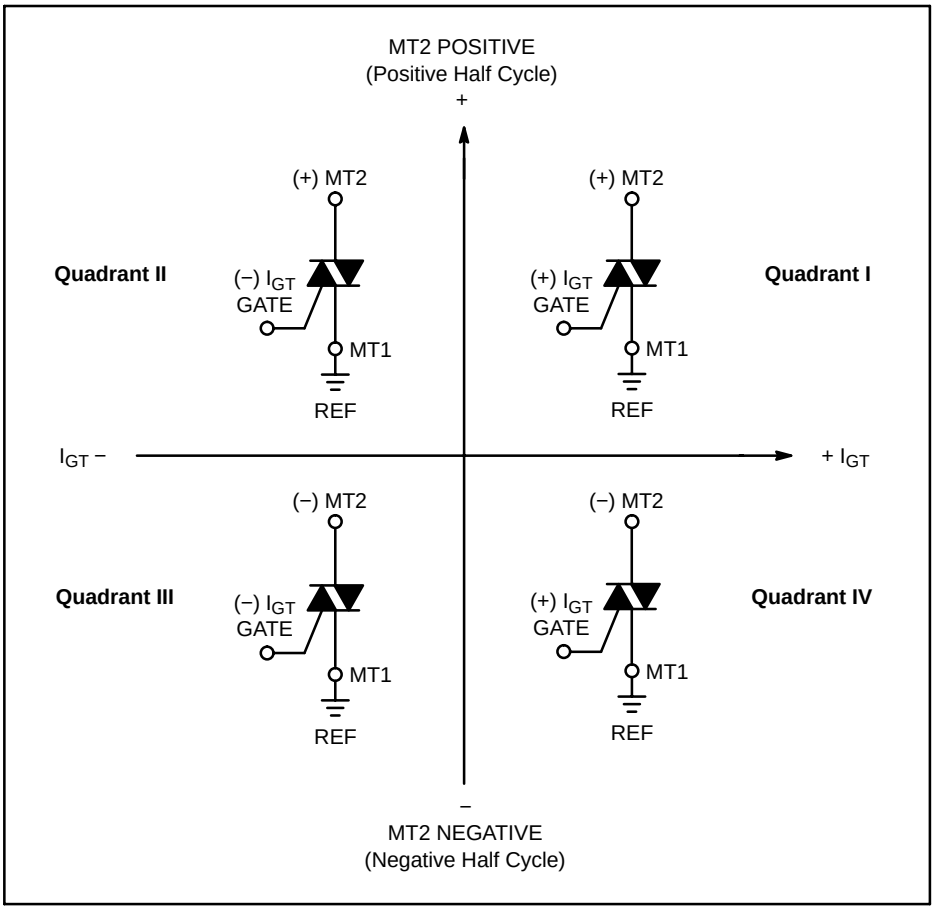
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Blocking Current (V_D = Rated V_{DRM}, V_{RRM}; Gate Open) T_J = 25°C T_J = +125°C	I_{DRM}, I_{RRM}	 − −	 − −	10 2.0	μA mA
ON CHARACTERISTICS					
Peak On-State Voltage (I_{TM} = ±11 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)	V_{TM}	−	1.2	1.65	V
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms) MT2(+), G(+) MT2(+), G(−) MT2(−), G(−) MT2(−), G(+)	I_{GT}	 − − − −	 12 12 20 35	 50 50 50 75	mA
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(−) MT2(−), G(−) MT2(−), G(+)	V_{GT}	 − − − −	 0.9 0.9 1.1 1.4	 2.0 2.0 2.0 2.5	V
Gate Non−Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, R_L = 100 Ω, T_J = +125°C) All Four Quadrants	V_{GD}	0.2	−	−	V
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = ±200 mA, T_C = +25°C)	I_H	−	6.0	50	mA
Turn-On Time (Rated V_{DRM}, I_{TM} = 11 A) (I_{GT} = 120 mA, Rise Time = 0.1 μs, Pulse Width = 2 μs)	t_{gt}	−	1.5	−	μs
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM}, I_{TM} = 14 A, Commutating di/dt = 5.0 A/ms, Gate Unenergized, T_C = 70°C)	dv/dt(c)	−	5.0	−	V/μs
Critical Rate of Rise of Off-State Voltage (V_D = Rated V_{DRM}, Exponential Voltage Rise, Gate Open, T_C = +70°C)	dv/dt	−	100	−	V/μs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in−phase signals (using standard AC lines) quadrants I and III are used.

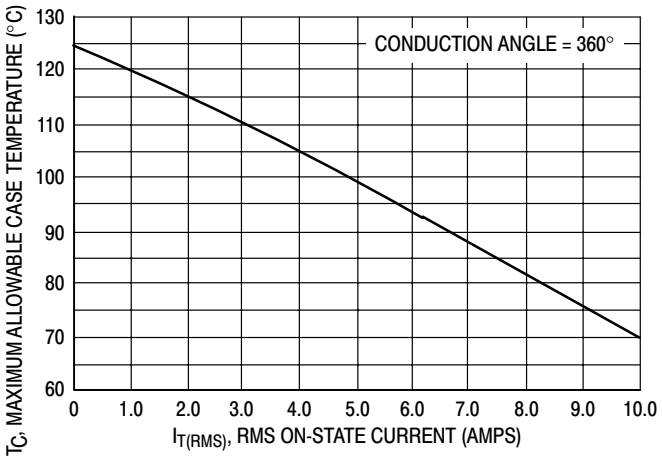


Figure 1. Current Derating

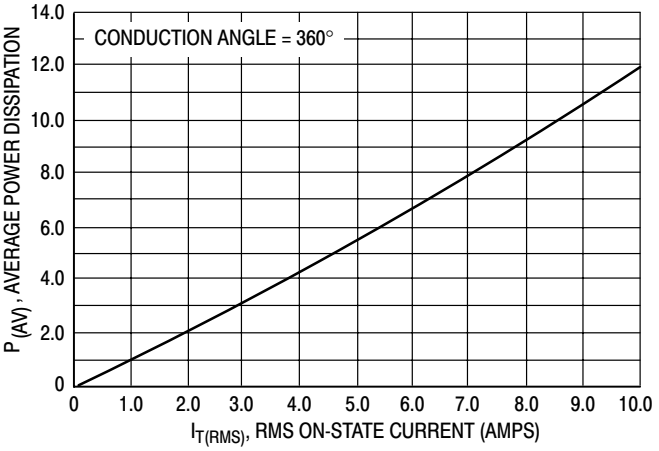


Figure 2. Power Dissipation

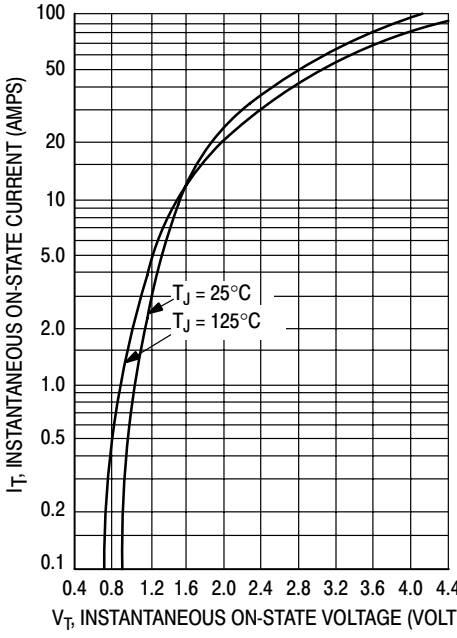


Figure 3. Maximum On−State Characteristics

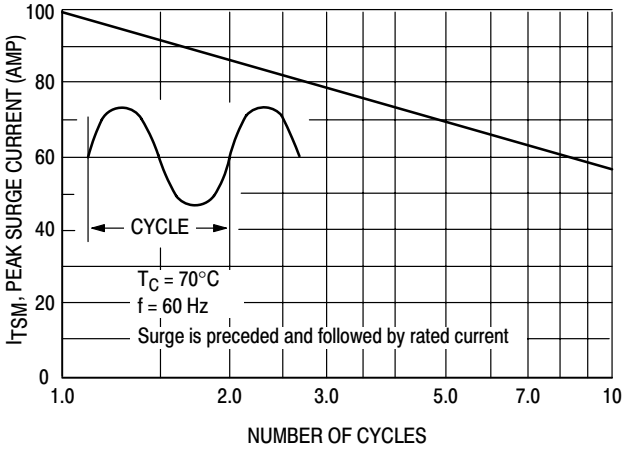


Figure 4. Maximum Non−Repetitive Surge Current

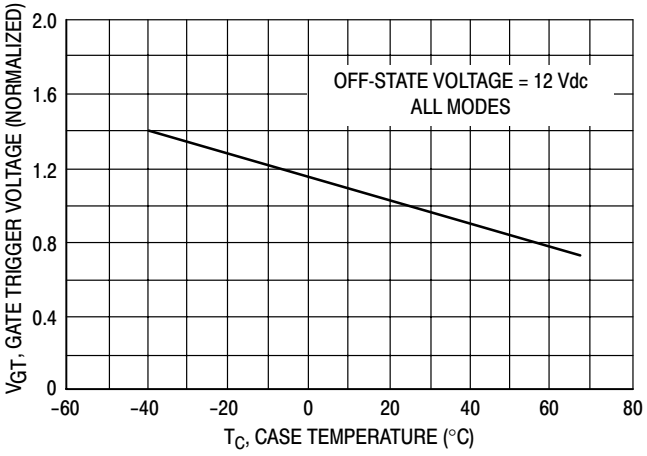


Figure 5. Typical Gate Trigger Voltage

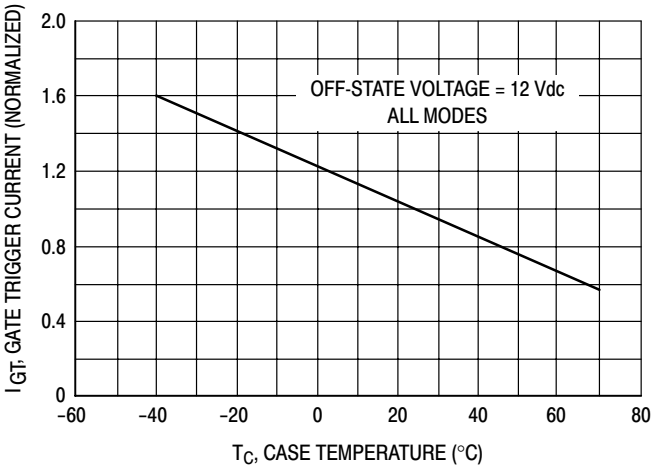


Figure 6. Typical Gate Trigger Current

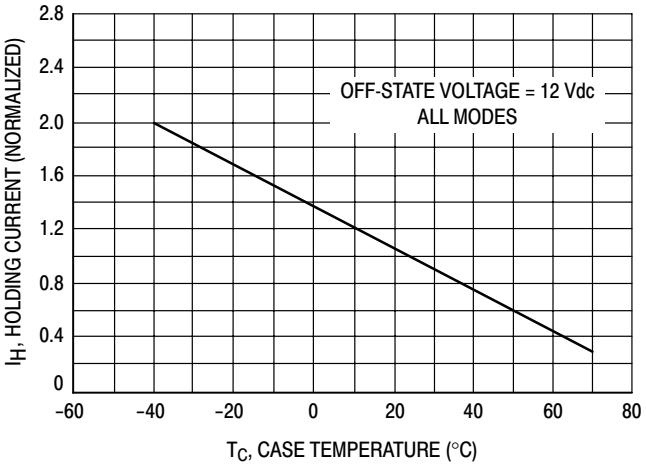


Figure 7. Typical Holding Current

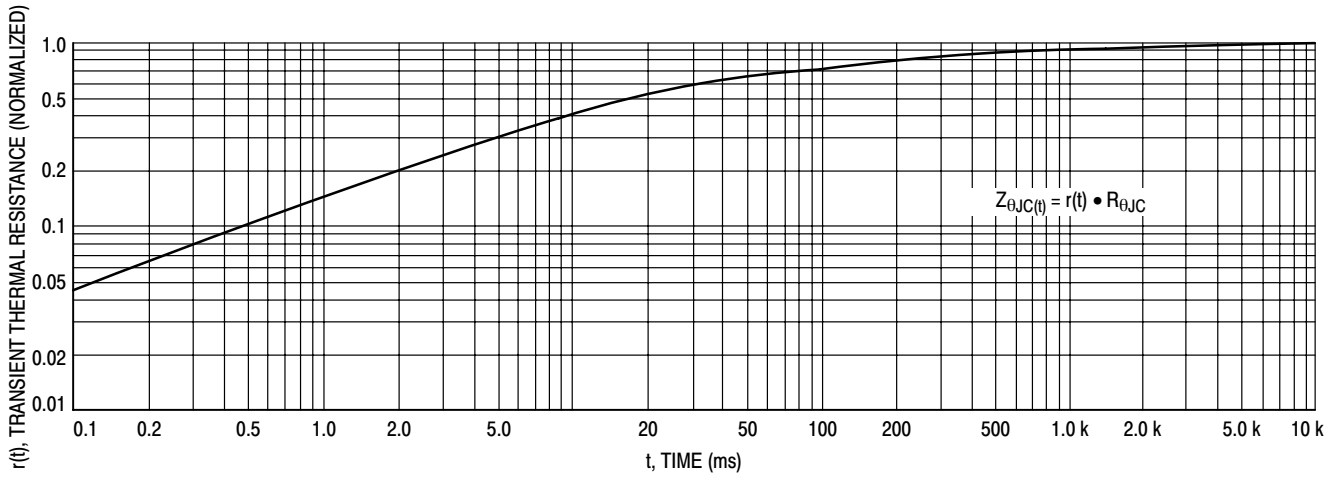
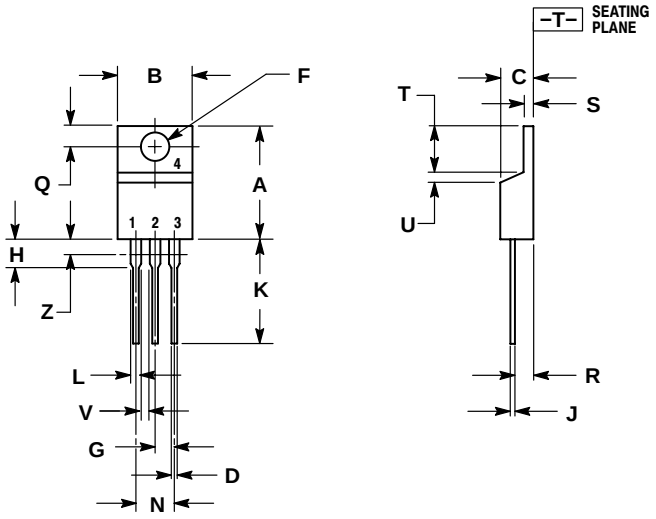


Figure 8. Thermal Response

PACKAGE DIMENSIONS

TO−220AB
CASE 221A−07
ISSUE AA



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5773−3850

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative